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YOR920000447US2 (13796A)

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Alessandro Callegari, et al.

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AC	5,312,565	11/01	Misra, et al.			
	6,037,003	3/14/00	Gordon, et al.			
	5,728,222	3/17/98	Barbee, et al.			
	5,648,113	7/15/97	Barbee, et al.			
	5,540,777	7/30/96	Barbee, et al.			
	5,431,734	7/11/95	Chapple-Sokol, et al.			
AC	4,097,314	6/27/78	Schlesier, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AC		Eble, R., et al., "Low Temperature Aluminum Oxide Deposition Using Trimethylaluminum", <u>Journal of Electronic Materials</u> , Vol. 12, No. 3, pp. 587-601 (1983);
AC		Kim, J.S., et al., "Fabrication of Aluminum Oxide Thin Films by a Low-Pressure Metalorganic Chemical Vapor Deposition Technique", <u>App. Phys. Lett.</u> , 62(7), February 15, 1993;

EXAMINER

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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AC			Fournier, J., et al., "Preparation and Characterization of Thin Films of Alumina by Metal-Organic Chemical Vapor Deposition", <u>Mat. Res. Bull.</u> , Vol. 23, pp. 31-36, 1988;
AC			Klein, T.M., et al. "Evidence of Aluminum Silicate Formation During Chemical Vapor Deposition of Amorphous Al ₂ O ₃ Thin Films on Si (100)", <u>Applied Physics Letters</u> , Vol. 75, No. 25, pp. 4001-4003, 1999;

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